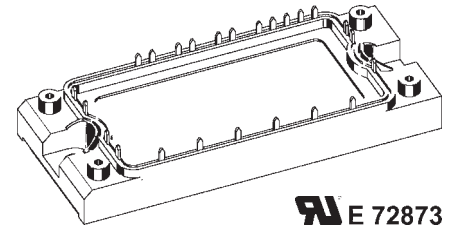
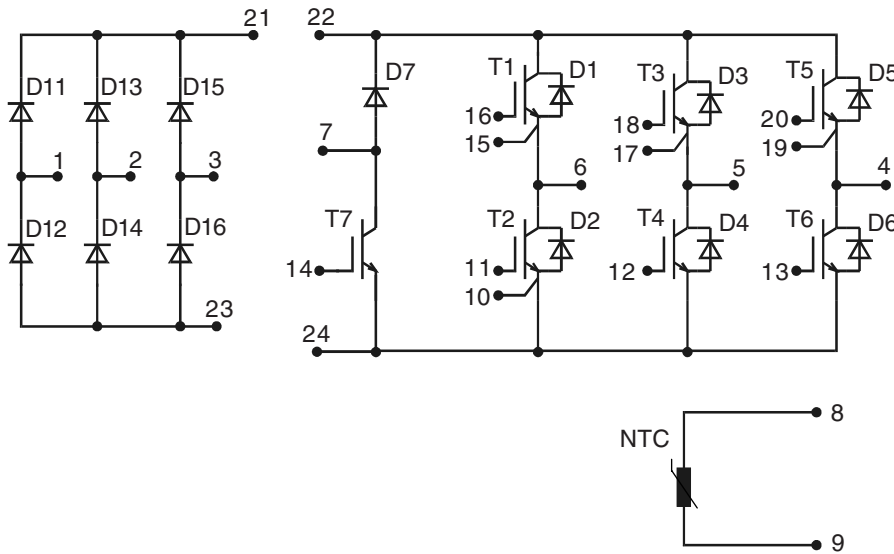


# Converter - Brake - Inverter Module (CBI2)


**RE 72873**

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600V$	$V_{CES} = 1200 V$	$V_{CES} = 1200 V$
$I_{DAVM} = 36 A$	$I_{C25} = 20 A$	$I_{C25} = 35 A$
$I_{FSM} = 300 A$	$V_{CE(sat)} = 2.3 V$	$V_{CE(sat)} = 2.1 V$

### Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings	
$V_{RRM}$		1600	V
$I_{FAV}$	$T_C = 80^\circ C$ ; sine 180°	25	A
$I_{DAVM}$	$T_C = 80^\circ C$ ; rectangular; $d = 1/3$	24	A
$I_{FSM}$	$T_{VJ} = 25^\circ C$ ; $t = 10 ms$ ; sine 50 Hz	300	A
$P_{tot}$	$T_C = 25^\circ C$	100	W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^\circ C$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 15 A$ ; $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$	1.3	1.3	1.6 V V
$I_R$	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.2	0.15 mA mA
$t_{rr}$	$V_R = 100 V$ ; $I_F = 15 A$ ; $di/dt = -15 A/\mu s$		1	$\mu s$
$R_{thJC}$	(per diode)			1.3 K/W

### Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- electric braking operation

### Features

- High level of integration - only one power semiconductor module required for the whole drive
- Fast rectifier diodes for enhanced EMC behaviour
- NPT IGBT technology with low saturation voltage, low switching losses, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

### Output Inverter T1 - T6

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	35	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	25	A
<b>RBSOA</b>	$V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$	$I_{CM} = 35$ $V_{CEK} \leq V_{CES}$	A
$t_{SC}$ <b>(SCSOA)</b>	$V_{CE} = V_{CES}$ ; $V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	180	W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 15\text{ A}$ ; $V_{GE} = 15\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1 2.3	2.6	V V
$V_{GE(th)}$	$I_C = 0.6\text{ mA}$ ; $V_{GE} = V_{CE}$	4.5	6.5	V
$I_{CES}$	$V_{CE} = V_{CES}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.9	0.9	mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ ; $V_{GE} = \pm 20\text{ V}$		200	nA
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}$ ; $I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$	100		ns
		70		ns
		500		ns
		70		ns
		2.3		mJ
		1.8		mJ
$C_{ies}$	$V_{CE} = 25\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; $f = 1\text{ MHz}$	1000		pF
$Q_{Gon}$	$V_{CE} = 600\text{ V}$ ; $V_{GE} = 15\text{ V}$ ; $I_C = 15\text{ A}$	70		nC
$R_{thJC}$	(per IGBT)		0.7	K/W

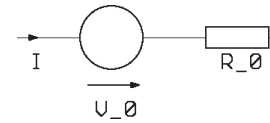
### Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^{\circ}\text{C}$	26	A
$I_{F80}$	$T_C = 80^{\circ}\text{C}$	17	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 15\text{ A}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.8	2.7 V V
$I_{RM}$ $t_{rr}$	$I_F = 15\text{ A}$ ; $di_F/dt = -400\text{ A}/\mu\text{s}$ ; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 600\text{ V}$ ; $V_{GE} = 0\text{ V}$		16	A
			130	ns
$R_{thJC}$	(per diode)			2.1 K/W

### Equivalent Circuits for Simulation

#### Conduction



#### D11 - D16

Rectifier Diode (typ. at  $T_J = 125^{\circ}\text{C}$ )  
 $V_0 = 1.08\text{ V}$ ;  $R_0 = 15\text{ m}\Omega$

#### T1 - T6 / D1 - D6

IGBT (typ. at  $V_{GE} = 15\text{ V}$ ;  $T_J = 125^{\circ}\text{C}$ )  
 $V_0 = 1.37\text{ V}$ ;  $R_0 = 62\text{ m}\Omega$

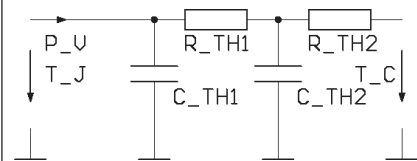
Free Wheeling Diode (typ. at  $T_J = 125^{\circ}\text{C}$ )  
 $V_0 = 1.32\text{ V}$ ;  $R_0 = 30\text{ m}\Omega$

#### T7 / D7

IGBT (typ. at  $V_{GE} = 15\text{ V}$ ;  $T_J = 125^{\circ}\text{C}$ )  
 $V_0 = 1.32\text{ V}$ ;  $R_0 = 131\text{ m}\Omega$

Free Wheeling Diode (typ. at  $T_J = 125^{\circ}\text{C}$ )  
 $V_0 = 1.39\text{ V}$ ;  $R_0 = 56\text{ m}\Omega$

#### Thermal Response



#### D11 - D16

Rectifier Diode (typ.)  
 $C_{th1} = 0.106\text{ J/K}$ ;  $R_{th1} = 1.06\text{ K/W}$   
 $C_{th2} = 0.79\text{ J/K}$ ;  $R_{th2} = 0.239\text{ K/W}$

#### T1 - T6 / D1 - D6

IGBT (typ.)  
 $C_{th1} = 0.156\text{ J/K}$ ;  $R_{th1} = 0.545\text{ K/W}$   
 $C_{th2} = 1.162\text{ J/K}$ ;  $R_{th2} = 0.155\text{ K/W}$

Free Wheeling Diode (typ.)  
 $C_{th1} = 0.065\text{ J/K}$ ;  $R_{th1} = 1.758\text{ K/W}$   
 $C_{th2} = 0.639\text{ J/K}$ ;  $R_{th2} = 0.342\text{ K/W}$

#### T7 / D7

IGBT (typ.)  
 $C_{th1} = 0.09\text{ J/K}$ ;  $R_{th1} = 0.954\text{ K/W}$   
 $C_{th2} = 0.809\text{ J/K}$ ;  $R_{th2} = 0.246\text{ K/W}$

Free Wheeling Diode (typ.)  
 $C_{th1} = 0.043\text{ J/K}$ ;  $R_{th1} = 2.738\text{ K/W}$   
 $C_{th2} = 0.54\text{ J/K}$ ;  $R_{th2} = 0.462\text{ K/W}$

**Brake Chopper T7**

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	20	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	15	A
<b>RBSOA</b>	$V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$	$I_{CM} = 20$ $V_{CEK} \leq V_{CES}$	A
$t_{SC}$ <b>(SCSOA)</b>	$V_{CE} = 720\text{ V}$ ; $V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$ ; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	105	W

Symbol	Conditions	Characteristic Values		
		$(T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 10\text{ A}$ ; $V_{GE} = 15\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.7	2.7 V V
$V_{GE(th)}$	$I_C = 0.4\text{ mA}$ ; $V_{GE} = V_{CE}$	4.5		6.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ ; $V_{GE} = 0\text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.3	0.5 mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ ; $V_{GE} = \pm 20\text{ V}$			200 nA
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}$ ; $I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}$ ; $R_G = 82\ \Omega$		50 40 290 60 1.2 1.1	ns ns ns ns mJ mJ
$C_{ies}$		$V_{CE} = 25\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; $f = 1\text{ MHz}$	600	pF
$Q_{Gon}$		$V_{CE} = 600\text{ V}$ ; $V_{GE} = 15\text{ V}$ ; $I_C = 10\text{ A}$	45	nC
$R_{thJC}$				1.2 K/W

**Brake Chopper D7**

Symbol	Conditions	Maximum Ratings	
$V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ to $150^{\circ}\text{C}$	1200	V
$I_{F25}$	$T_C = 25^{\circ}\text{C}$	17	A
$I_{F80}$	$T_C = 80^{\circ}\text{C}$	11	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 10\text{ A}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.9	2.9 V V
$I_R$	$V_R = V_{RRM}$ ; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.07	0.06 mA mA
$I_{RM}$ $t_{tr}$	$I_F = 10\text{ A}$ ; $di_F/dt = -400\text{ A}/\mu\text{s}$ ; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 600\text{ V}$		13 110	A ns
$R_{thJC}$				3.2 K/W

### Temperature Sensor NTC

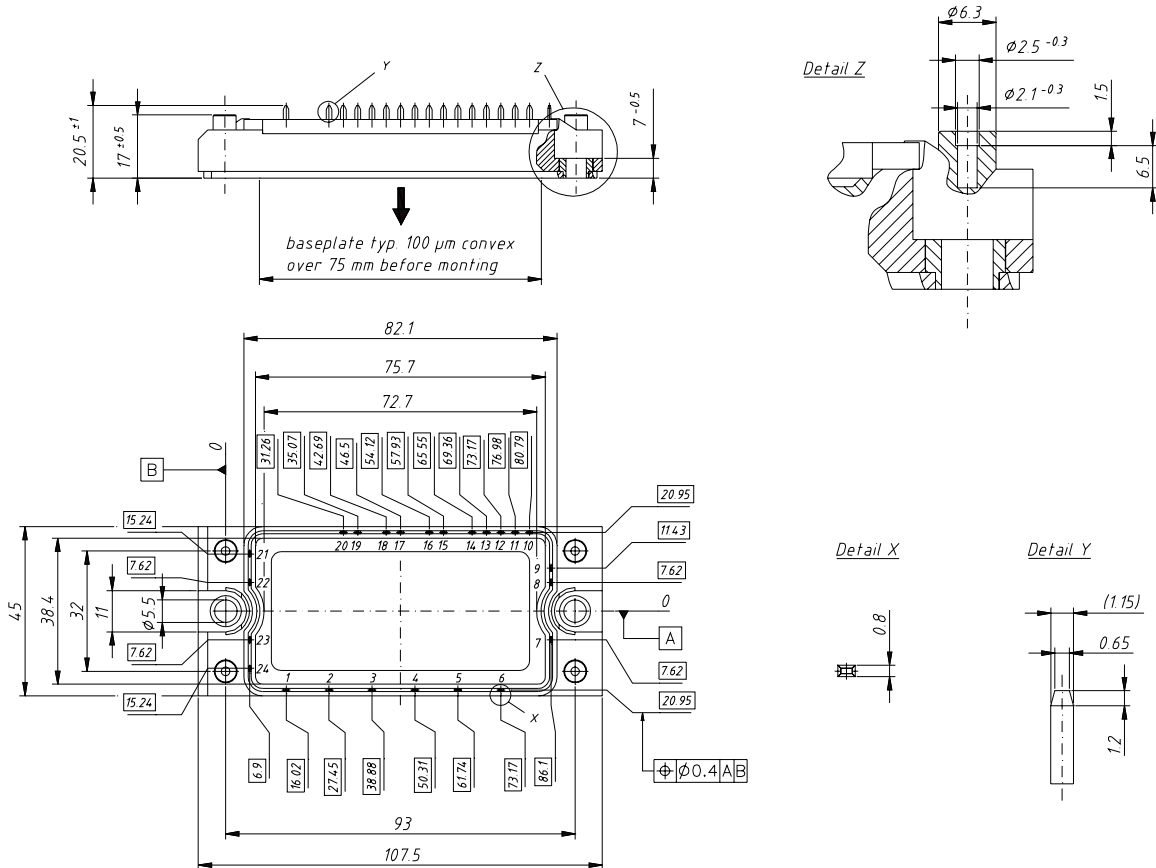
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	T = 25°C	4.75	5.0	5.25 kΩ
$B_{25/50}$			3375	K

### Module

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$	Operating	-40...+125	°C
$T_{JM}$		150	°C
$T_{stg}$		-40...+125	°C
$V_{ISOL}$	$I_{ISOL} \leq 1$ mA; 50/60 Hz	2500	V~
$M_d$	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			5	mΩ
$d_S$	Creepage distance on surface	6		mm
$d_A$	Strike distance in air	6		mm
$R_{thCH}$	with heatsink compound	0.02		K/W
Weight		180		g

### Dimensions in mm (1 mm = 0.0394")



**Input Rectifier Bridge D11 - D16**

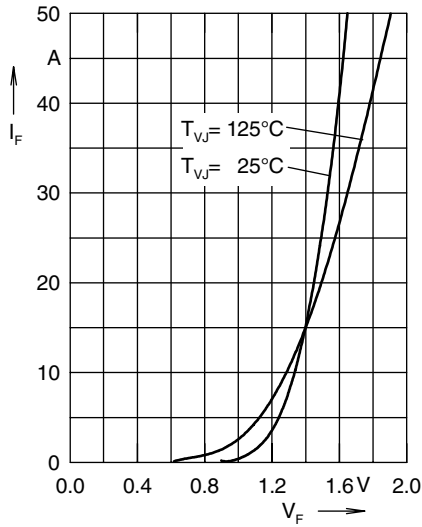


Fig. 1 Forward current versus voltage drop per diode

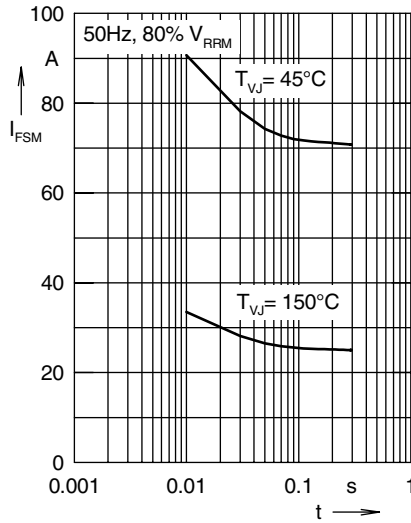


Fig. 2 Surge overload current

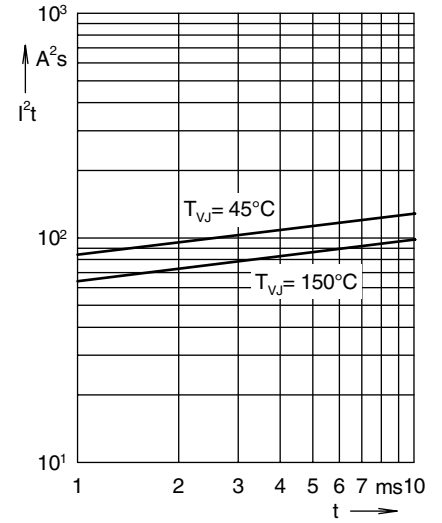


Fig. 3 I<sup>2</sup>t versus time per diode

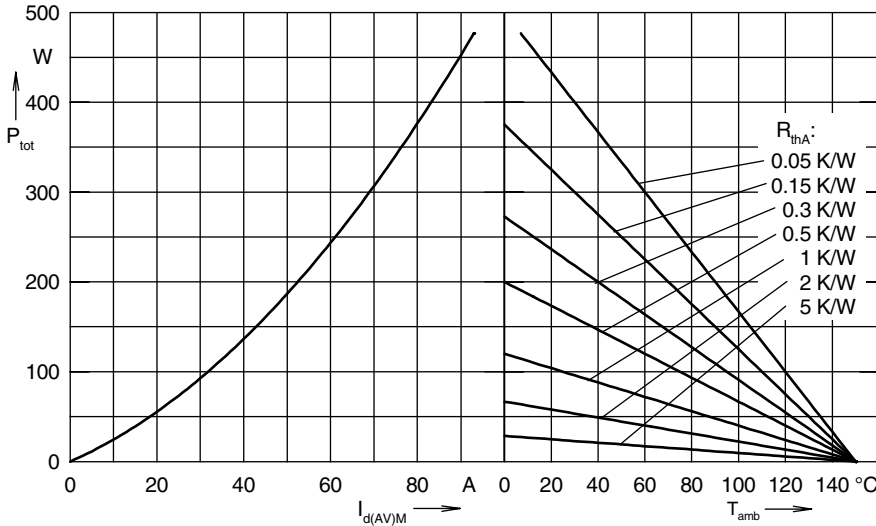


Fig. 4 Power dissipation versus direct output current and ambient temperature, sin 180°

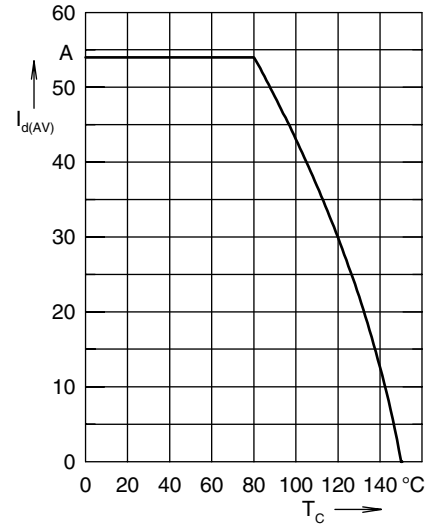


Fig. 5 Max. forward current versus case temperature

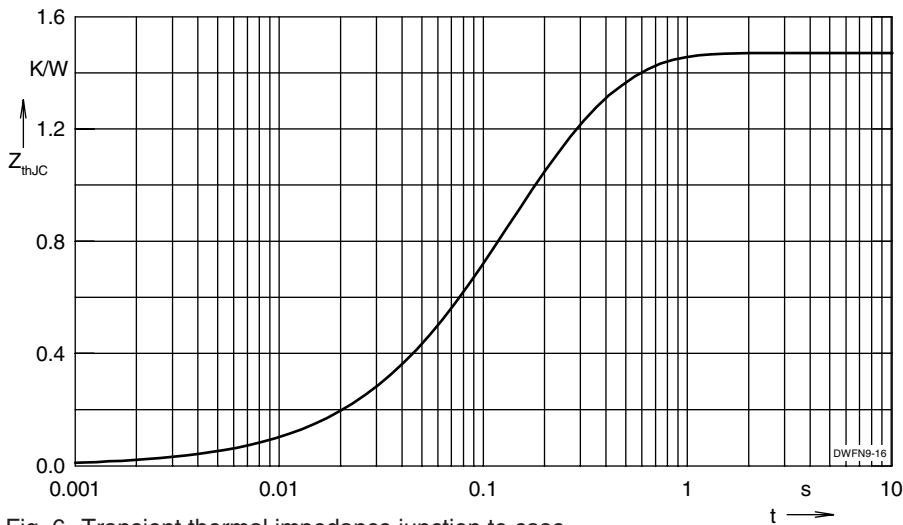


Fig. 6 Transient thermal impedance junction to case

**Output Inverter T1 - T6 / D1 - D6**

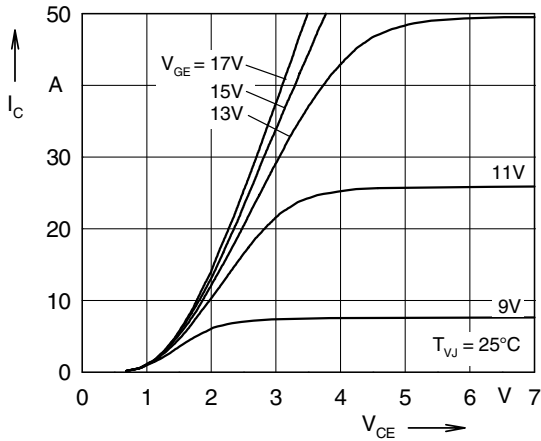


Fig. 7 Typ. output characteristics

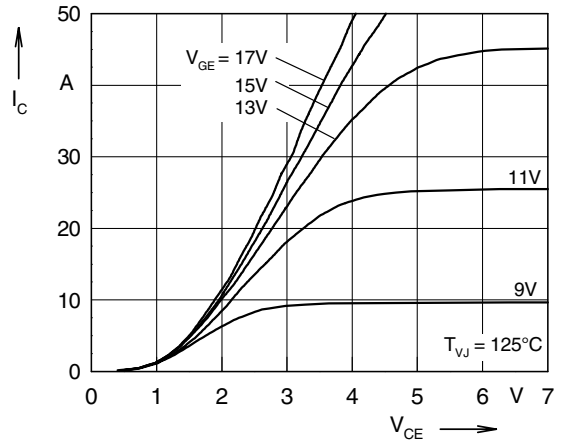


Fig. 8 Typ. output characteristics

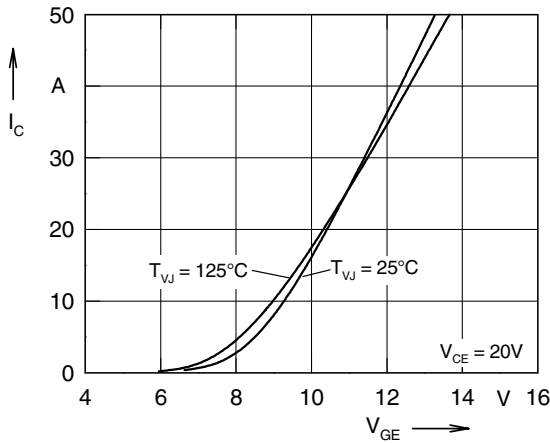


Fig. 9 Typ. transfer characteristics

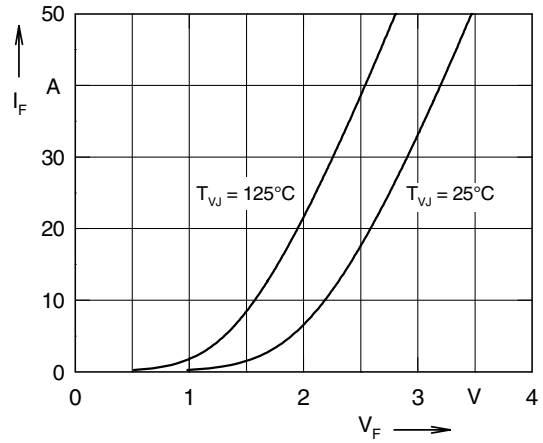


Fig. 10 Typ. forward characteristics of free wheeling diode

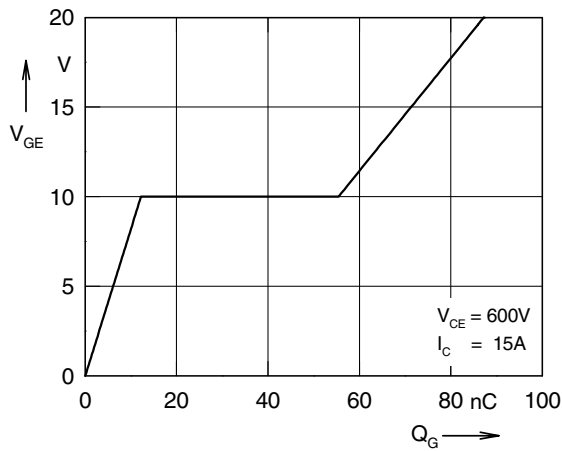


Fig. 11 Typ. turn on gate charge

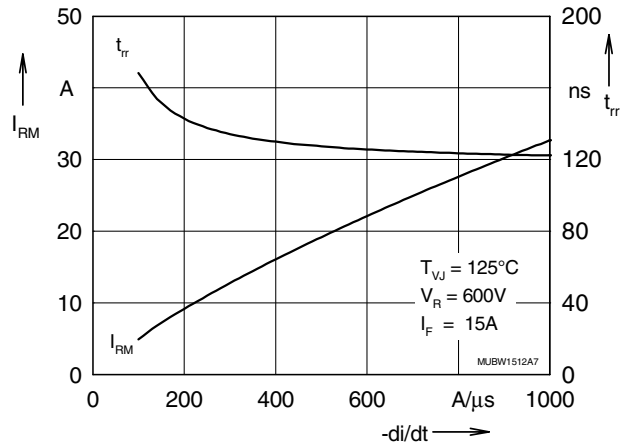


Fig. 12 Typ. turn off characteristics of free wheeling diode

Output Inverter T1 - T6 / D1 - D6

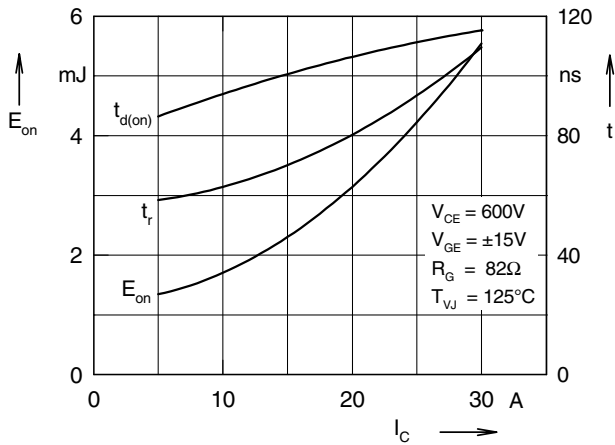


Fig. 13 Typ. turn on energy and switching times versus collector current

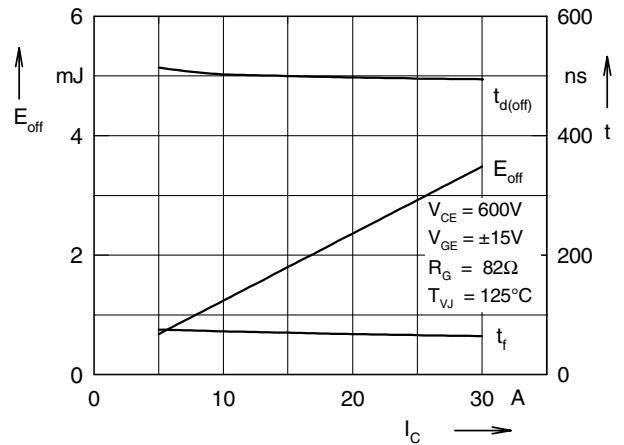


Fig. 14 Typ. turn off energy and switching times versus collector current

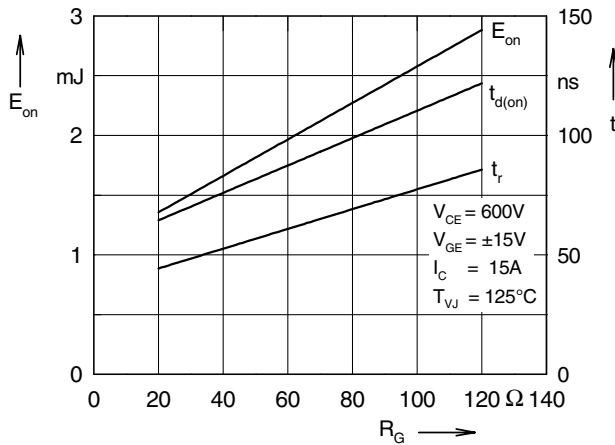


Fig. 15 Typ. turn on energy and switching times versus gate resistor

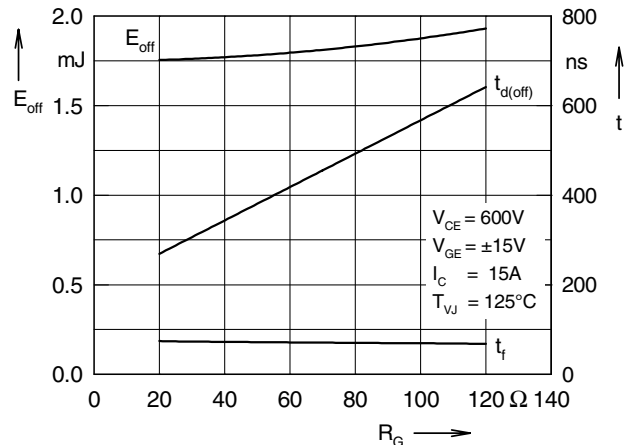


Fig. 16 Typ. turn off energy and switching times versus gate resistor

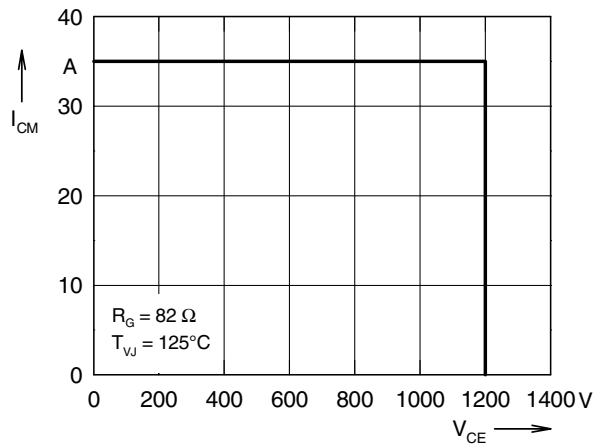


Fig. 17 Reverse biased safe operating area RBSOA

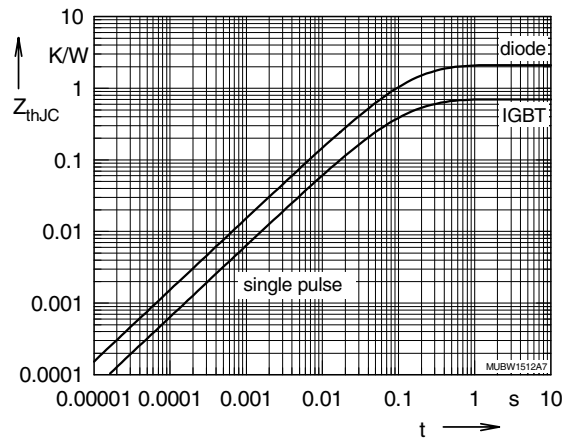


Fig. 18 Typ. transient thermal impedance

Brake Chopper T7 / D7

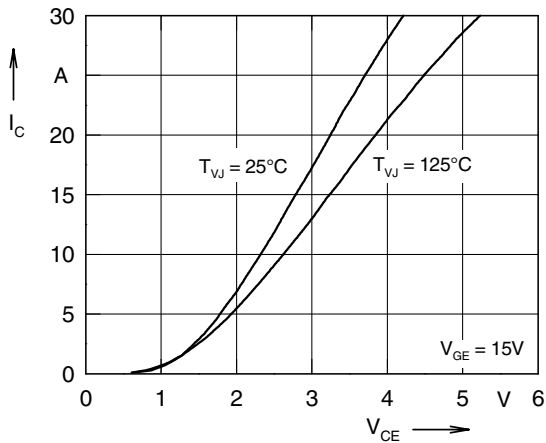


Fig. 19 Typ. output characteristics

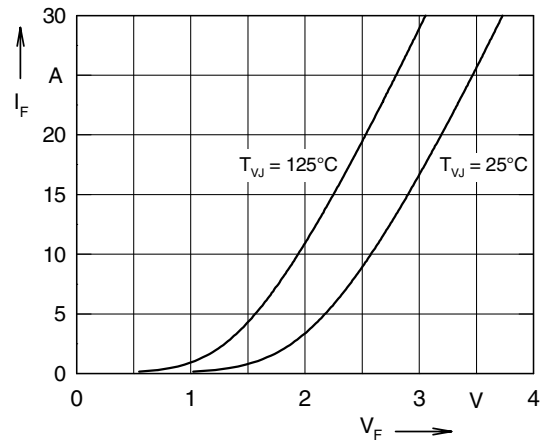


Fig. 20 Typ. forward characteristics of free wheeling diode

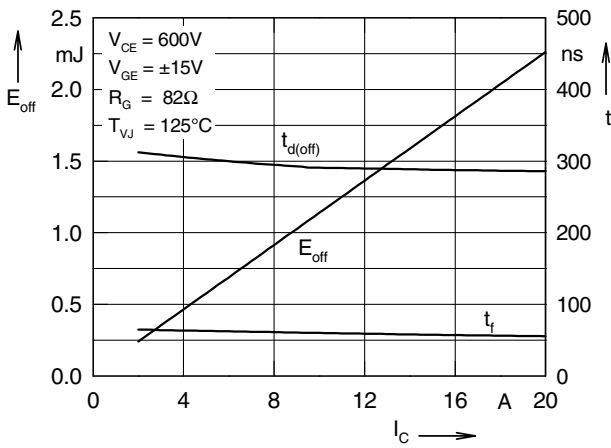


Fig. 21 Typ. turn off energy and switching times versus collector current

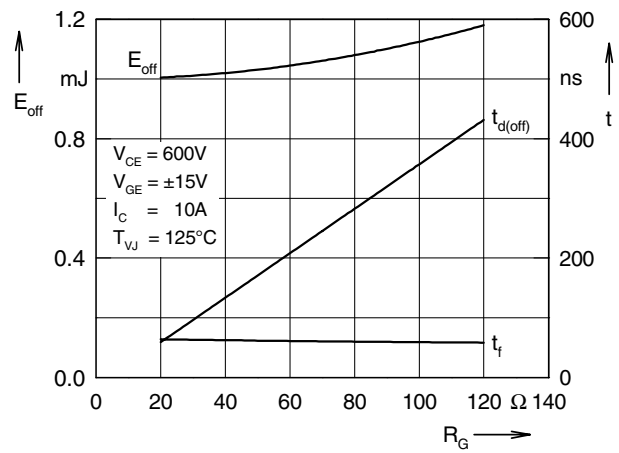


Fig. 22 Typ. turn off energy and switching times versus gate resistor

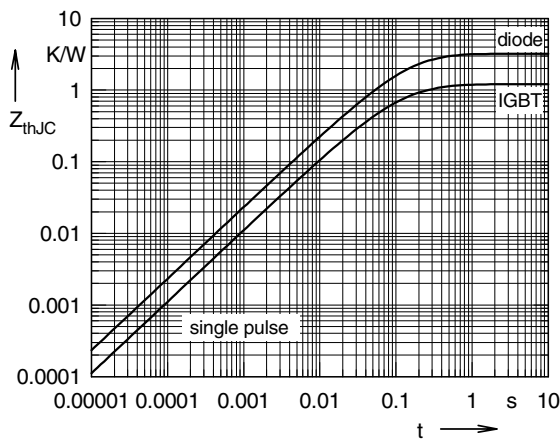


Fig. 23 Typ. transient thermal impedance

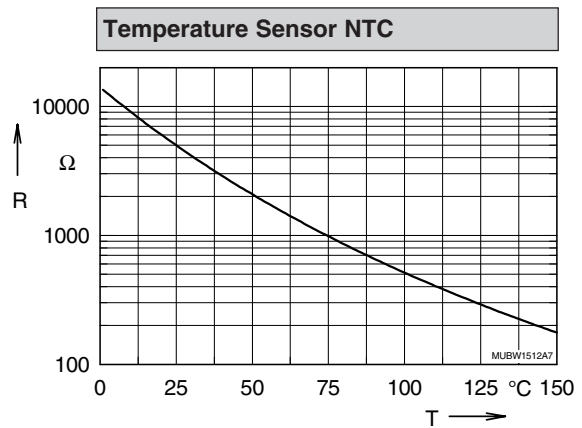


Fig. 24 Typ. thermistorresistance versus temperature



## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9